

REMARKS

The Examiner's Office Action of December 15, 2004 has been received and its contents reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application.

By this Amendment, claims 1, 3, 6, 9 and 32-34 have been amended to improve form. Accordingly, claims 1-45 are pending for consideration, of which claims 1, 3, 6, 9 and 32-34 are independent.

Referring now to the detailed Office Action, claims 1-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted of prior art (hereinafter "AAPA") in view of U.S. Patent No. 4,090,219 to Ernstoff et al. (hereinafter "Ernstoff"), U.S. Patent No. 4,750,813 to Ohwada et al. (hereinafter "Ohwada") and U.S. Patent No. 6,784,034 to Choi. Claims 10-31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's AAPA in view of Ernstoff and Ohwada as applied to claims 3 and 9 above, and further in view of U.S. Patent No. 5,528,262 to McDowall et al. (hereinafter "McDowall"). Claims 32-34 are rejected under 35 U.S.C. 103(a) as being unpatentable over AAPA in view of Ernstoff, Ohwada, Choi and U.S. Patent No. 5,327,229 to Konno et al. (hereinafter "Konno"). Claims 35-45 are rejected under 35 U.S.C. 103(a) as being unpatentable over AAPA in view of Ernstoff, Ohwada, Choi and Konno, as applied to claims 32-34 above, and further in view of McDowall. In view of the amendments to the claims and the comments to follow, Applicants respectfully traverse this rejection.

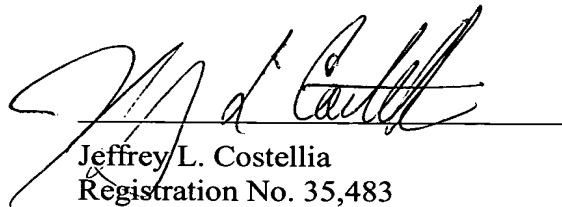
For example, with regard to independent claim 1, Applicants have amended the independent claim 1 to recite that at least one of the first thin film transistors, the second thin film transistors and the third thin film transistor has a low concentration impurity region adjacent to the channel forming region. Also, independent claims 3 and 6 have been amended to recite that the thin film transistor has a low concentration impurity region adjacent to the channel forming region. Independent claim 9 has been amended to recite that at least one of the first thin film transistors and the second thin film transistors has a low concentration impurity region adjacent to the channel forming region. These features are supported, for example by line 8-22 of page 37 and Fig. 19. Applicants respectfully submit

that none of Applicant's Admitted Prior Art, Ernstoff, Ohwada and Choi teach or suggest these features. Accordingly, Applicants respectfully request reconsideration and withdrawal of the rejection.

Also, regarding independent claims 32-34, Applicants have amended the claims to recite that at least one of the first thin film transistors and the second thin film transistors has a low concentration impurity region adjacent to the channel forming region. Applicants submit that this feature is not disclosed in any one of Applicant's Admitted Prior Art, Ernstoff, Ohwada, Choi and Konno. Accordingly, Applicants respectfully request reconsideration and withdrawal of the rejection.

While the present application is now believed to be in condition for allowance, should the Examiner find some issue to remain unresolved, or should any new issues arise which could be eliminated through discussions with Applicants' representative, then the Examiner is invited to contact the undersigned by telephone in order that the further prosecution of this application can thereby be expedited.

Respectfully submitted,



Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
401 9th Street, Suite 900
Washington, D.C. 20004-2128
(202) 585-8000
(202) 585-8080 FAX

JLC/BCO